

NPN Epitaxial Planar Transistor

BTC1510I3

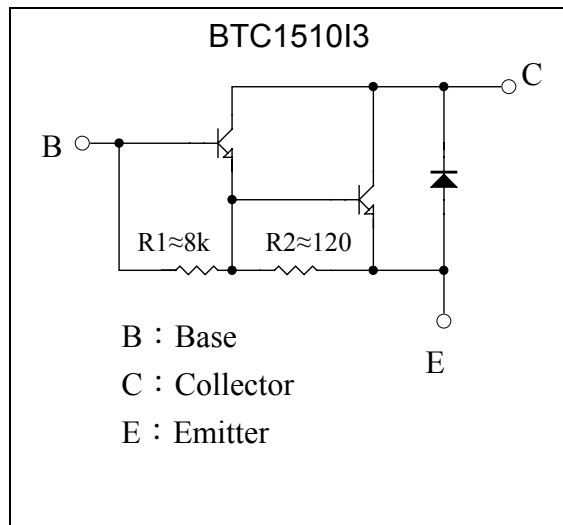
Description

The BTC1510I3 is a NPN Darlington transistor, designed for general purpose amplifier and low speed switching application.

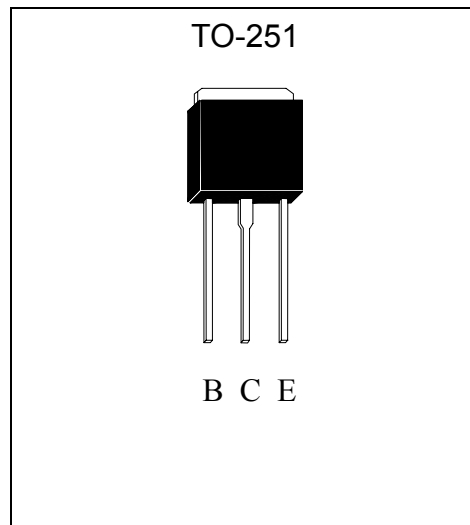
Features:

- High BV_{CEO}
- Low $V_{CE(SAT)}$
- High current gain
- Monolithic construction with built-in base-emitter shunt resistors
- Pb-free package

Equivalent Circuit



Outline



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	150	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C (DC)	10	A
	I _C (Pulse)	15 *1	
Power Dissipation	Pd(T _A =25°C)	1.75	W
	Pd(T _C =25°C)	20	
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

Note : *1. Single Pulse Pw=100ms

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	150	-	-	V	I _C =100μA, I _E =0
BV _{CEO}	150	-	-	V	I _C =1mA, I _B =0
I _{CEO}	-	-	200	μA	V _{CE} =150V, I _E =0
I _{CBO}	-	-	200	μA	V _{CB} =150V, I _E =0
I _{EBO}	-	-	2	mA	V _{EB} =5V, I _C =0
*V _{CE(sat)} 1	-	-	1.5	V	I _C =5A, I _B =10mA
*V _{CE(sat)} 2	-	-	3	V	I _C =10A, I _B =100mA
*V _{CE(sat)} 3	-	-	1.5	V	I _C =5A, I _B =2.5mA
*V _{BE(sat)}	-	-	2	V	I _C =5A, I _B =5mA
*V _{BE(on)} 1	-	-	2.8	V	V _{CE} =3V, I _C =5A
*V _{BE(on)} 2	-	-	4.5	V	V _{CE} =3V, I _C =10A
*V _{FEC}	-	-	3	V	I _C =5A
*h _{FE1}	2	-	20	K	V _{CE} =3V, I _C =5A
*h _{FE2}	100	-	-	-	V _{CE} =3V, I _C =10A

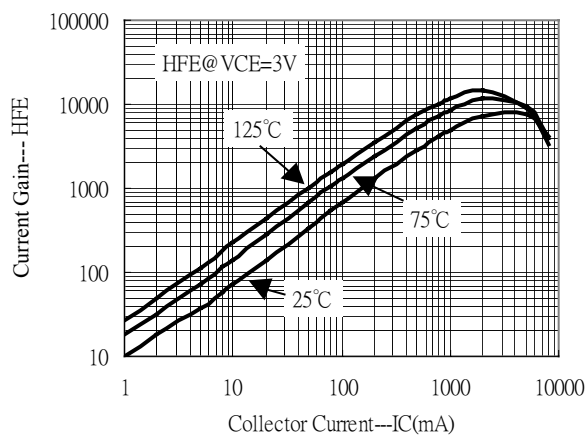
*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

Classification of V_{CE(sat)} 1

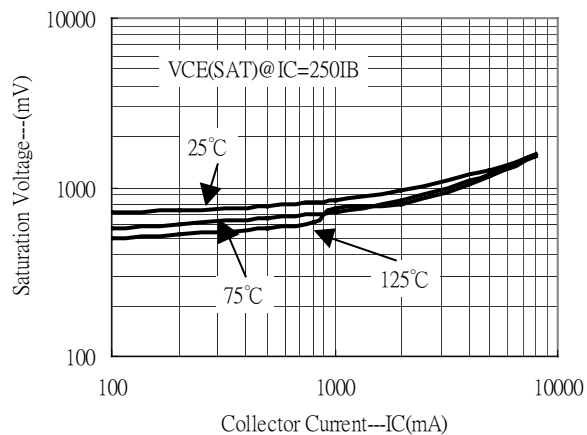
Rank	KA	N
Range	<1.1V	1.1~1.5V

Characteristic Curves

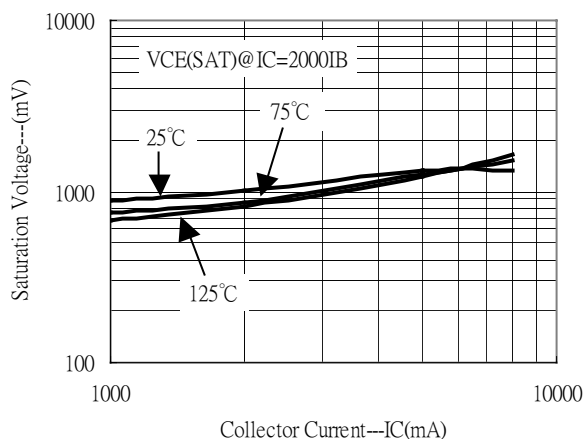
Current Gain vs Collector Current



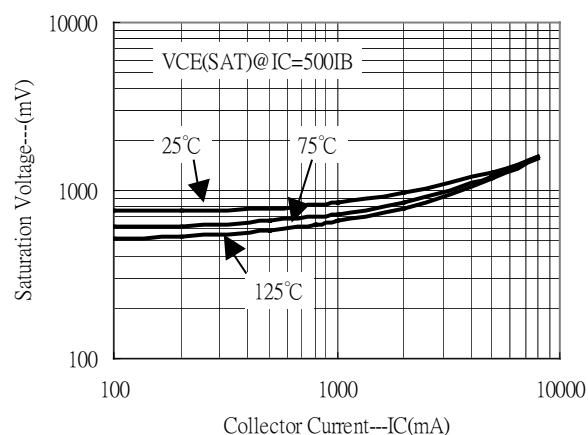
Saturation Voltage vs Collector Current



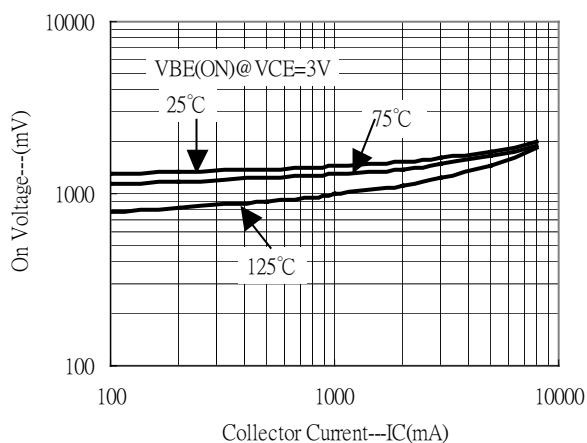
Saturation Voltage vs Collector Current



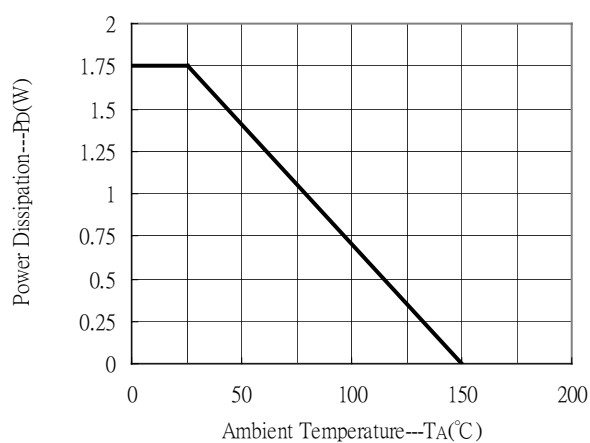
Saturation Voltage vs Collector Current



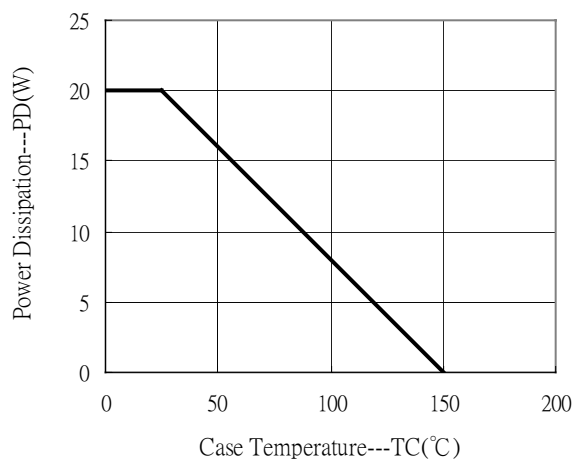
Saturation Voltage vs Collector Current



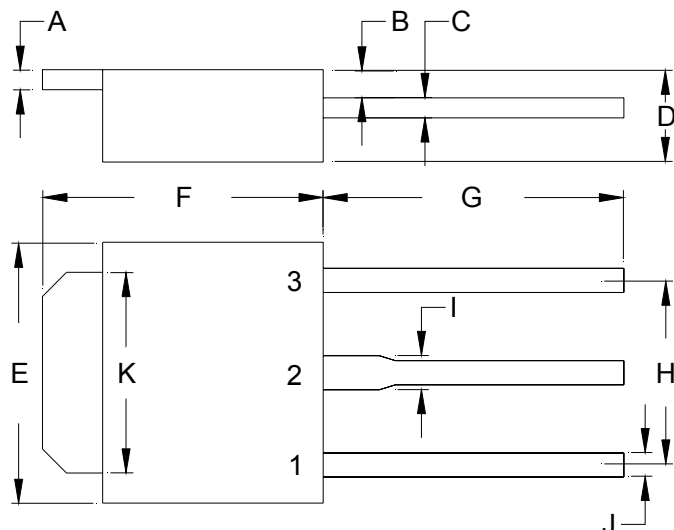
Power Derating Curve



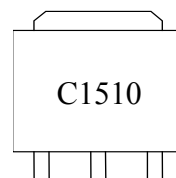
Power Derating Curve



TO-251 Dimension



Marking:



Style: Pin 1.Base 2.Collector 3.Emitter

3-Lead TO-251 Plastic Package
CYStek Package Code: I3

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.2559	-	6.50	-
B	0.0354	0.0591	0.90	1.50	H	-	*0.1811	-	*4.60
C	0.0177	0.0236	0.45	0.60	I	-	0.0354	-	0.90
D	0.0866	0.0945	2.20	2.40	J	-	0.0315	-	0.80
E	0.2520	0.2677	6.40	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2677	0.2835	6.80	7.20					

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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